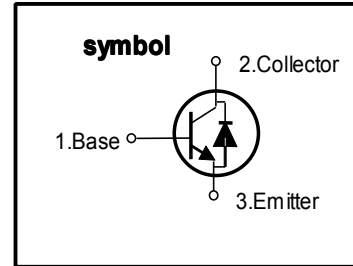


High Voltage Fast -Switching NPN Power Transistor

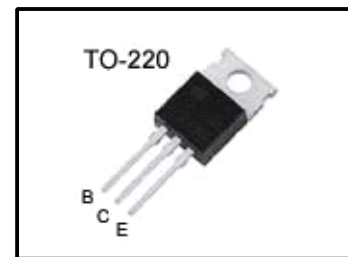
Features

- Very High Switching Speed
- High Voltage Capability
- Wide Reverse Bias SOA
- Built-in free wheeling diode



General Description

This Device is designed for high Voltage ,High speed switching Characteristics required such as lighting system,switching mode power supply.



Absolute Maximum Ratings

Symbol	Parameter	Test conditions	Value	Units
V _{CES}	Collector-Emitter Voltage	V _{BE} =0	700	V
V _{CEO}	Collector-Emitter Voltage	I _B =0	400	V
V _{EBO}	Emitter-Base Voltage	I _C =0	9.0	V
I _C	Collector Current		1.5	A
I _{CP}	Collector pulse Current		3.0	A
I _B	Base Current		0.75	A
I _{BM}	Base peak Current	t _p =5ms	1.5	A
P _C	Total Dissipation at T _c *=25 °C		40	W
	Total Dissipation at T _a *=25 °C		1.2	
T _J	Operation Junction Temperature		-40~150	°C
T _{STG}	Storage Temperature		-40~150	°C

T_c :Case temperature (good cooling)

T_a :Ambient temperature (without heat sink)

Thermal characteristics

Symbol	Parameter	Value	Units
R _{θJC}	Thermal Resistance Junction to Case	3.12	°C/W
R _{θJA}	Thermal Resistance Junction to Ambient	8.9	°C/W

Electrical Characteristics(T_c=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Value			Units
			Min	Typ	Max	
I _{EBO}	Emitter Cut-off Current	V _{BE} =9V	-	-	20	μA
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _B =0, I _C =10mA	400	-	-	V
V _{CE(sat)}	Collector -Emitter Saturation Voltage	I _C =1.0A, I _B =0.2A	-	-	0.5	V
		I _C =2.0A, I _B =0.5A	-	-	0.6	
		I _C =4.0A, I _B =1.0A	-	-	1.0	
V _{BE(sat)}	Base -Emitter Saturation Voltage	I _C =1.0A, I _B =0.2A	-	-	1.2	V
		I _C =2.0A, I _B =0.5A	-	-	1.6	
hFE	DC Current Gain	I _C =500A, V _{CE} =5V	10	-	40	
		I _C =1mA, V _{CE} =5V	9	-	-	
ts	Storage Time	I _C =0.5A, V _{CC} =5V	-	-	4	μs
tf	Fall Time	(UI9600A)	-	-	0.8	
f _T	Current Gain Bandwidth Product	I _C =0.5A, V _{CE} =10V	4	-	-	MHz
V _F	Diode Forward Voltage	I _F =2A	-	-	2	V
C _{OB}	Output Capacitance	I _C =0.5A, V _{CB} =10V	-	21	-	pF

Note:

Pulse Test :Pulse width 300, Duty cycle 2%

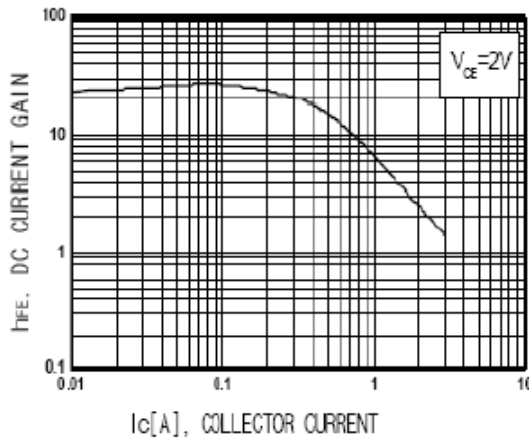


Fig.1 DC Current Gain

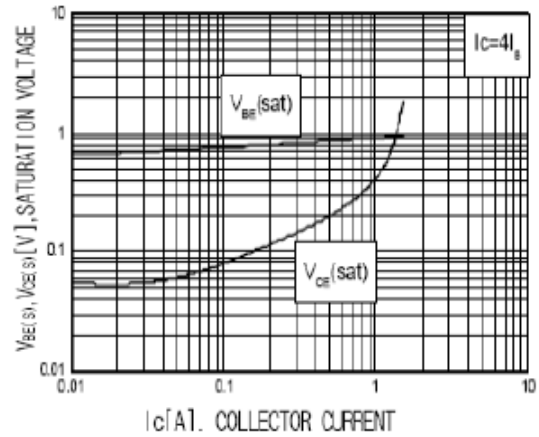


Fig.2 Saturation Voltage

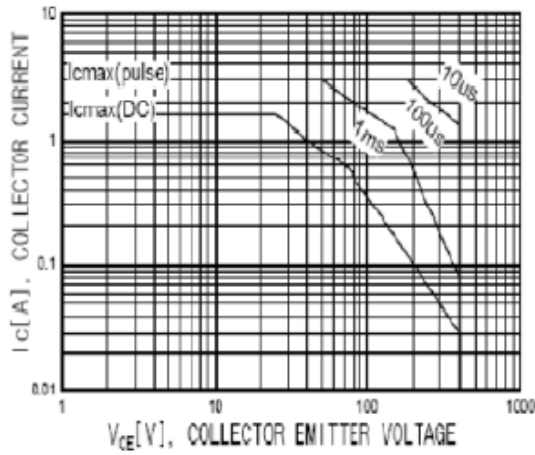


Fig.3 Safe Operation

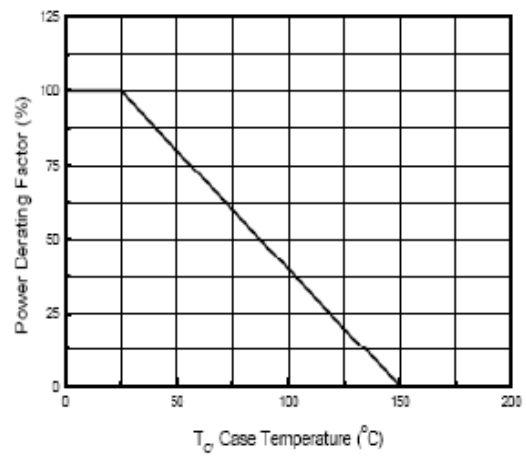
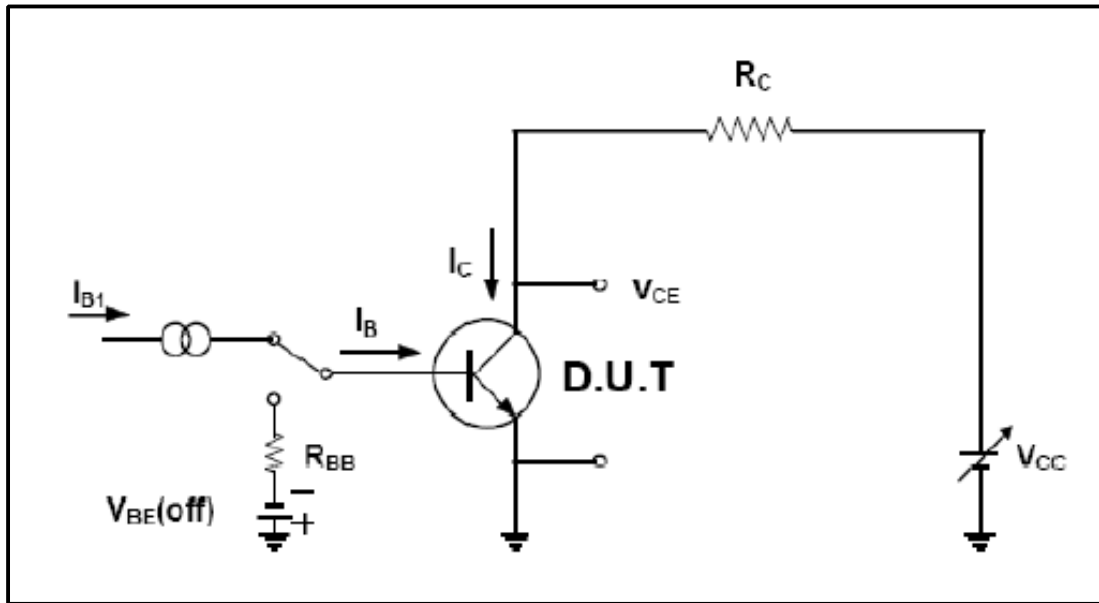
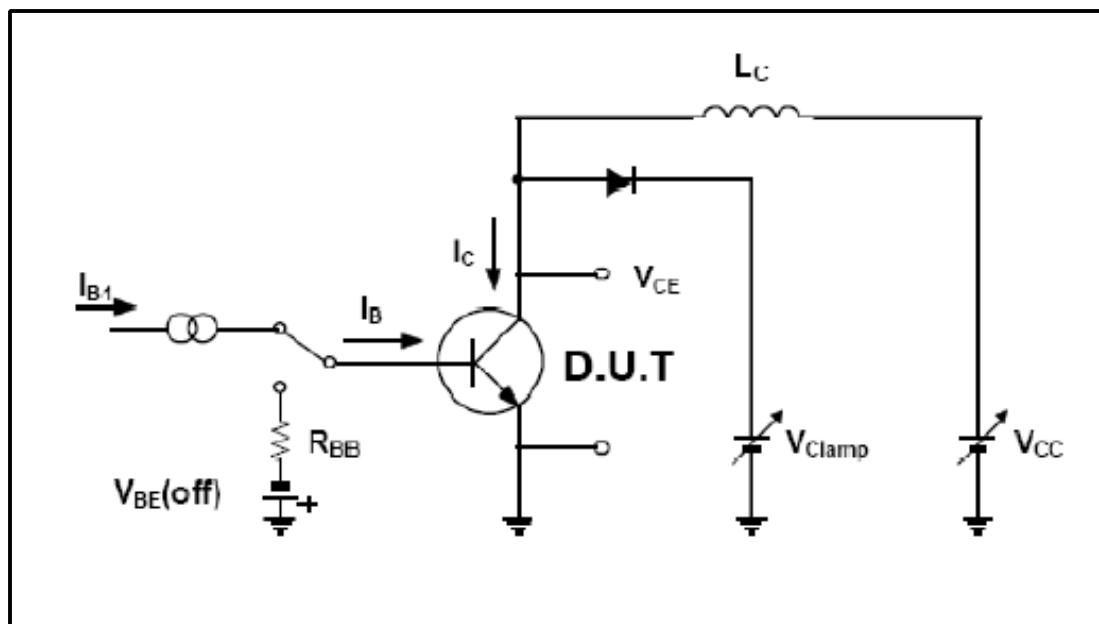


Fig.4 Power Derating



Resistive Load Switching Test Circuit



Inductive Load Switching & RBSOA Test Circuit

TO-220 Package Dimension

Unit:mm

